



ORDER DESCRIPTION

1. Object of the contract

The subject of the contract is a thermoelectric cooler in the amount of

No	Product name	Qty
1.	GaAs Wafer; Dia: 3", Thickness: 1,1 (100)+/-0.2 ; VGF	50

2. Parameters

2.1. Detailed scope of the subject

Product name		Parameter	Specification
GaAs	Diameter 3" Thickness: 1.1. mm	Grade:	Epi-ready grade
	Top Ceramics (cold)	Growth method	VGF
		Conduct type	Semi-insulating (S-I)
		Dopant	undoped
	bottom ceramics	Orientation:	(100)±0.2°
	pellets	Primary Flat:	EJ (0-1-1)
	terminal wires AWG30	Secondary Flat	EJ (0-11)
	Assembling Solder	Resistivity:	min 1E8 Ω/cm
	TEC bonding	EPD (Average)::	<5000/cm ² max
	Header	Mobility:	Min: 4870 Max: 6050 cm ² /V*cm
	TEC mounting	Surface Finish:	Surface side 1 Epi-ready grade Surface side 2 polish
Height	Packaging:	ePAK	